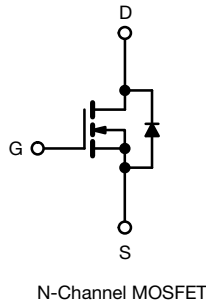
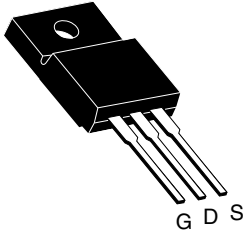


D Series Power MOSFET

TO-220 FULLPAK

FEATURES

- Optimal design
 - Low area specific on-resistance
 - Low input capacitance (C_{iss})
 - Reduced capacitive switching losses
 - High body diode ruggedness
 - Avalanche energy rated (UIS)
- Optimal efficiency and operation
 - Low cost
 - Simple gate drive circuitry
 - Low figure-of-merit (FOM): $R_{on} \times Q_g$
 - Fast switching
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	550	
$R_{DS(on)}$ max. (Ω) at 25 °C	$V_{GS} = 10$ V	0.85
Q_g max. (nC)	30	
Q_{gs} (nC)	4	
Q_{gd} (nC)	7	
Configuration	Single	

APPLICATIONS

- Consumer electronics
 - Displays (LCD or plasma TV)
- Server and telecom power supplies
 - SMPS
- Industrial
 - Welding
 - Induction heating
 - Motor drives
- Battery chargers

ORDERING INFORMATION

Package	TO-220 FULLPAK
Lead (Pb)-free	SiHF8N50D-E3


ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	500	V
Gate-Source Voltage	V_{GS}	± 30	
Gate-Source Voltage AC ($f > 1$ Hz)		30	
Continuous Drain Current ($T_J = 150$ °C) ^e	V_{GS} at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current ^a	I_{DM}	18	
Linear Derating Factor		0.26	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	56	mJ
Maximum Power Dissipation	P_D	33	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
Drain-Source Voltage Slope	dV/dt	$T_J = 125$ °C	24
Reverse Diode dV/dt ^d		0.37	V/ns
Soldering Recommendations (Peak temperature) ^c	For 10 s	300	°C
Mounting Torque	M3 screw	0.6	Nm

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 2.3$ mH, $R_g = 25$ Ω , $I_{AS} = 7$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, starting $T_J = 25$ °C.
- Limited by maximum junction temperature.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	3.8	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		500	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 250\text{ }\mu\text{A}$		-	0.58	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		3	-	5	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	μA
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 4\text{ A}$	-	0.70	0.85	Ω
Forward Transconductance ^a	g_{fs}	$V_{DS} = 20\text{ V}, I_D = 4\text{ A}$		-	3	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$		-	527	-	pF
Output Capacitance	C_{oss}			-	52	-	
Reverse Transfer Capacitance	C_{rss}			-	8	-	
Effective Output Capacitance, Energy Related ^b	$C_{o(er)}$			-	46	-	
Effective Output Capacitance, Time Related ^c	$C_{o(tr)}$	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$		-	64	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 4\text{ A}, V_{DS} = 400\text{ V}$	-	15	30	nC
Gate-Source Charge	Q_{gs}			-	4	-	
Gate-Drain Charge	Q_{gd}			-	7	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 4\text{ A}, R_g = 9.1\text{ }\Omega, V_{GS} = 10\text{ V}$		-	13	26	ns
Rise Time	t_r			-	16	32	
Turn-Off Delay Time	$t_{d(off)}$			-	17	34	
Fall Time	t_f			-	11	22	
Gate Input Resistance	R_g	$f = 1\text{ MHz}, \text{open drain}$		-	1.8	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	8	A
Pulsed Diode Forward Current	I_{SM}			-	-	32	
Diode Forward Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 4\text{ A}, V_{GS} = 0\text{ V}$		-	-	1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 4\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 20\text{ V}$		-	308	-	ns
Reverse Recovery Charge	Q_{rr}			-	1.8	-	μC
Reverse Recovery Current	I_{RRM}			-	11	-	A

Note

- Repetitive rating; pulse width limited by maximum junction temperature.
- $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
- $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

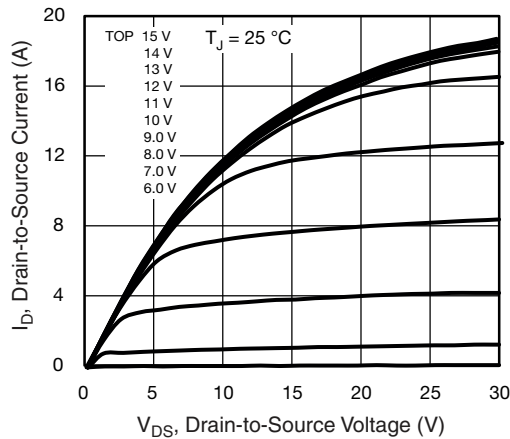


Fig. 1 - Typical Output Characteristics

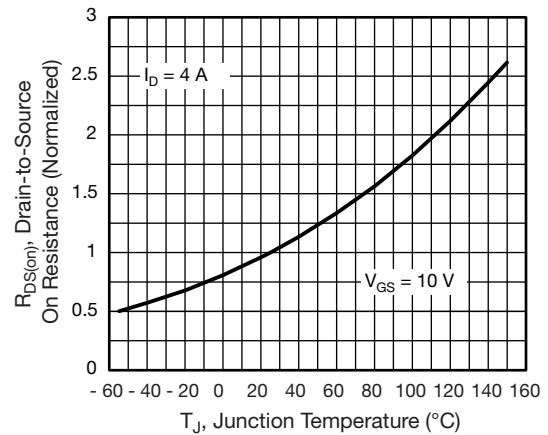


Fig. 4 - Normalized On-Resistance vs. Temperature

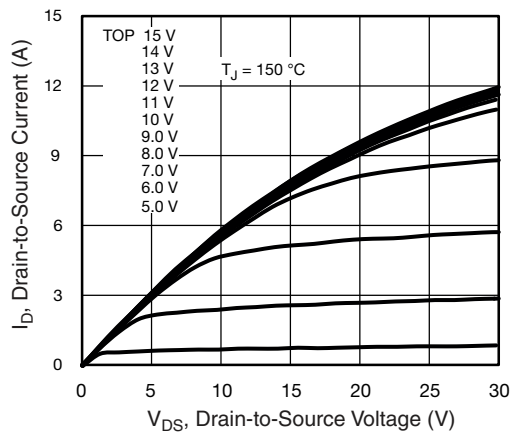


Fig. 2 - Typical Output Characteristics

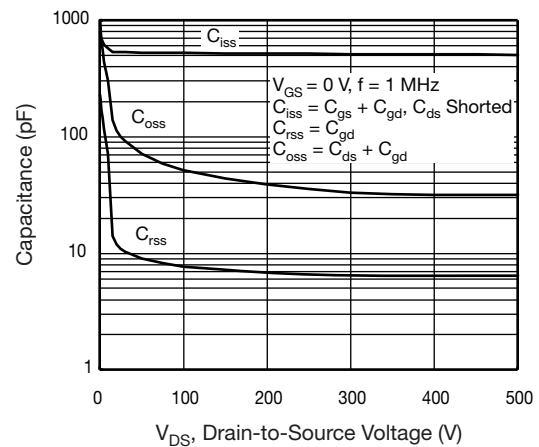


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

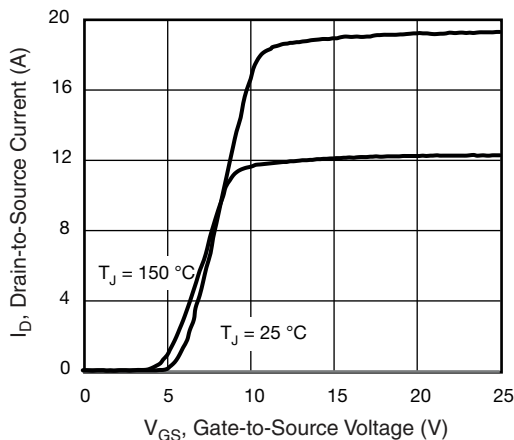


Fig. 3 - Typical Transfer Characteristics

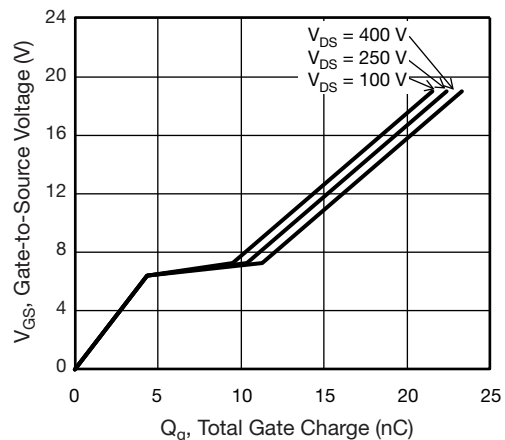


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

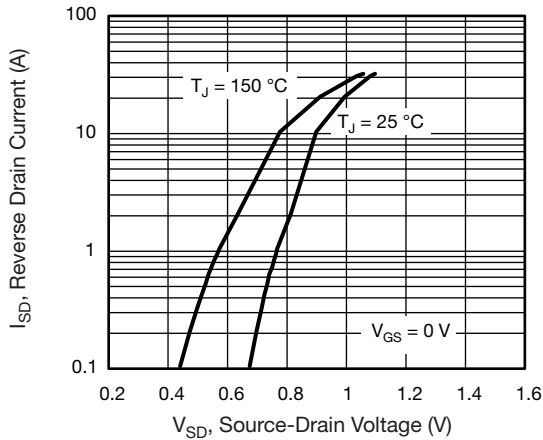


Fig. 7 - Typical Source-Drain Diode Forward Voltage

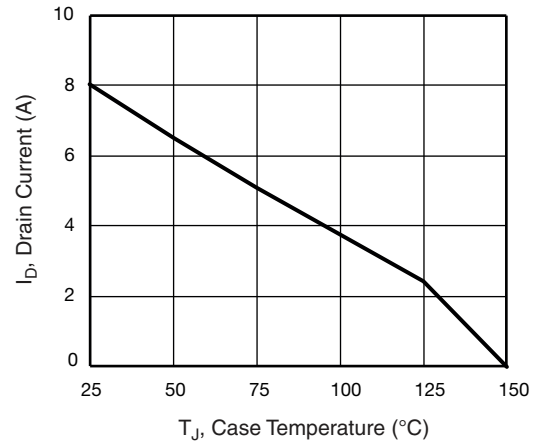


Fig. 9 - Maximum Drain Current vs. Case Temperature

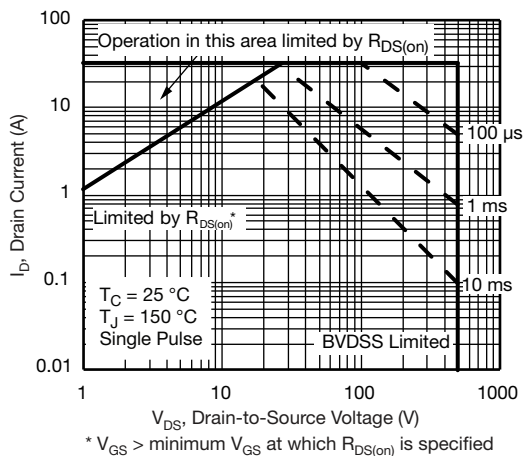


Fig. 8 - Maximum Safe Operating Area

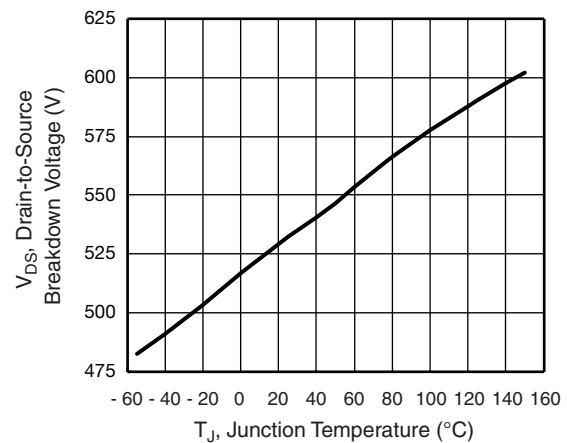


Fig. 10 - Typical Drain-to-Source Voltage vs. Temperature

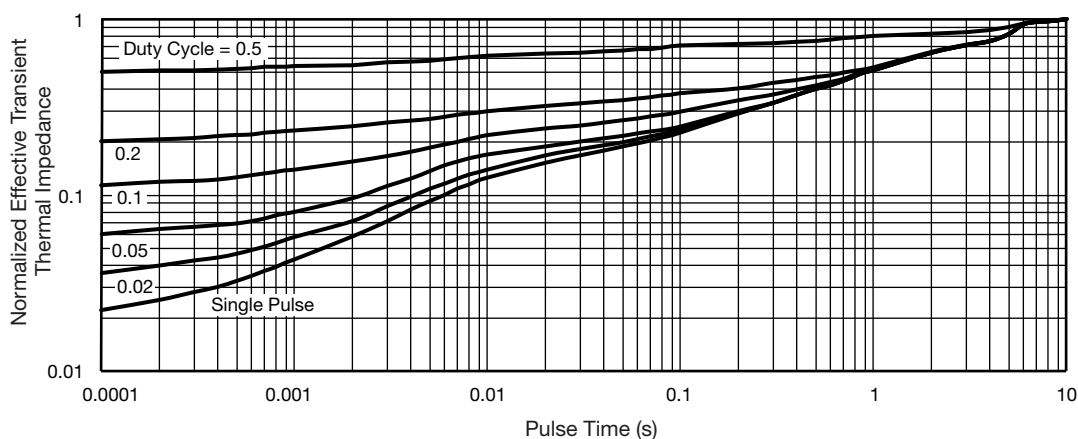


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

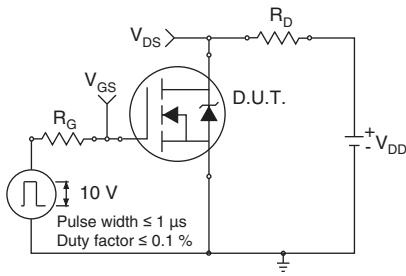


Fig. 12 - Switching Time Test Circuit

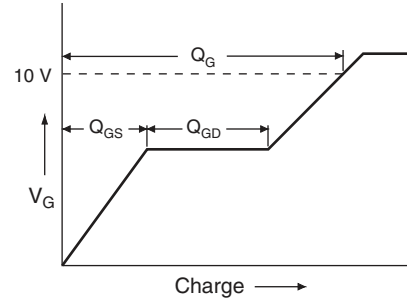


Fig. 16 - Basic Gate Charge Waveform

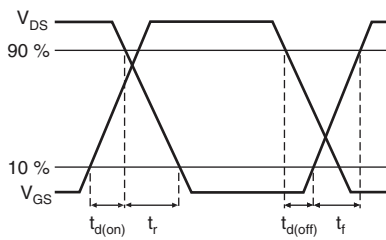


Fig. 13 - Switching Time Waveforms

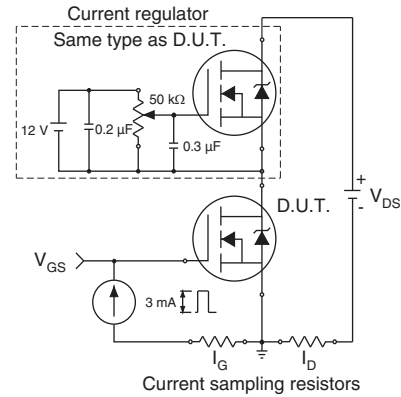


Fig. 17 - Gate Charge Test Circuit

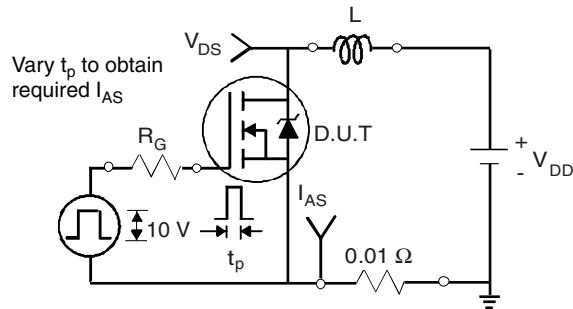


Fig. 14 - Unclamped Inductive Test Circuit

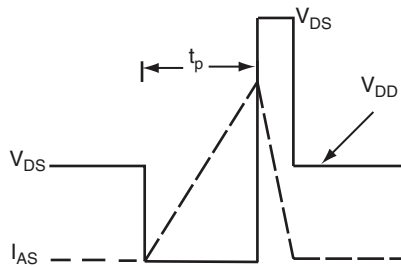
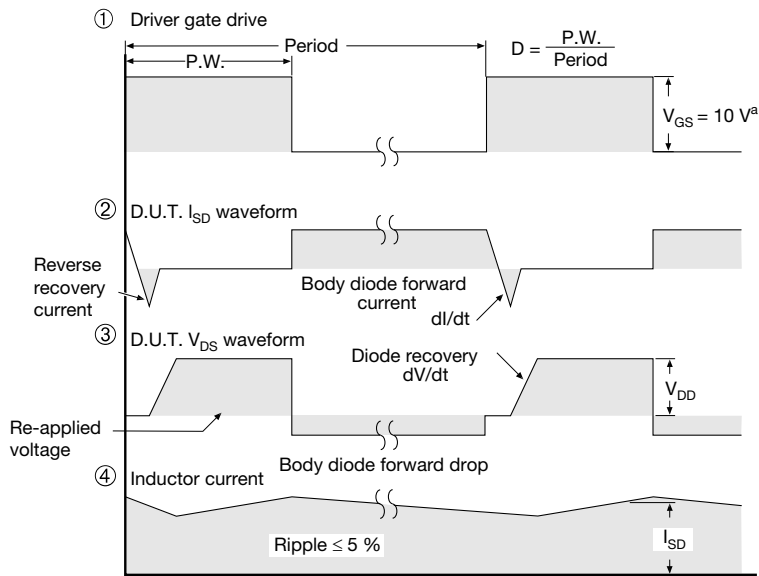
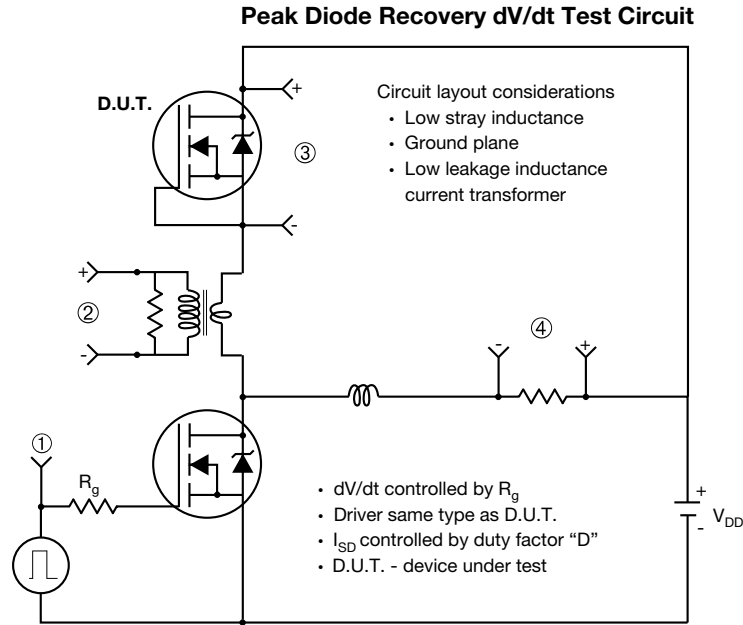


Fig. 15 - Unclamped Inductive Waveforms



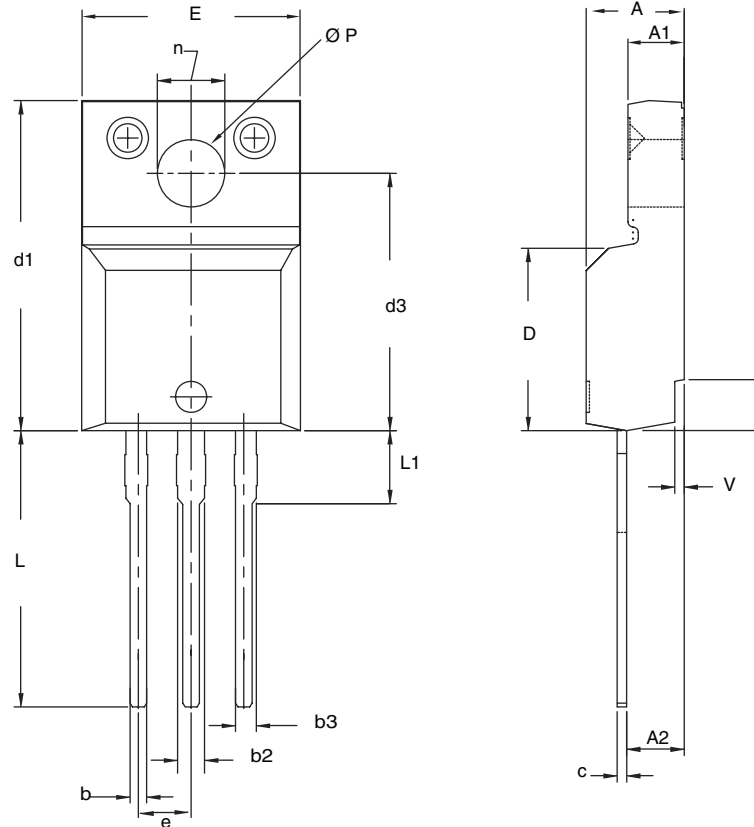
Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 18 - For N-Channel

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TO-220 FULLPAK (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
v	0.400	0.500	0.016	0.020

ECN: X09-0126-Rev. B, 26-Oct-09
 DWG: 5972

Notes

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet $C_{pk} > 1.33$.
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.



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